

BCR8PM-12LD

Triac

Medium Power Use

REJ03G1564-0100 Rev.1.00 Jul 06, 2007

Features

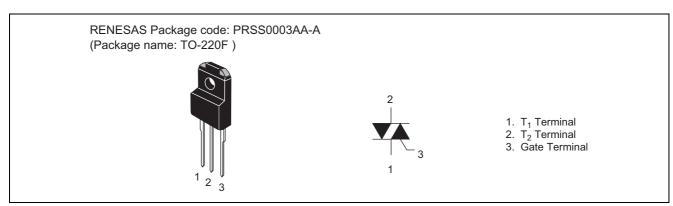
 $\begin{array}{ll} \bullet & I_{T \, (RMS)} : 8 \; A \\ \bullet & V_{DRM} : 600 \; V \end{array}$

• I_{FGTI} , I_{RGTI} , I_{RGTIII} : 50 mA

• Viso : 2000 V

- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Type

Outline



Applications

Motor control, heater control

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	700	V

BCR8PM-12LD

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	8	А	Commercial frequency, sine full wave 360° conduction, Tc = 85°C
Surge on-state current	I _{TSM}	48	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	9.5	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

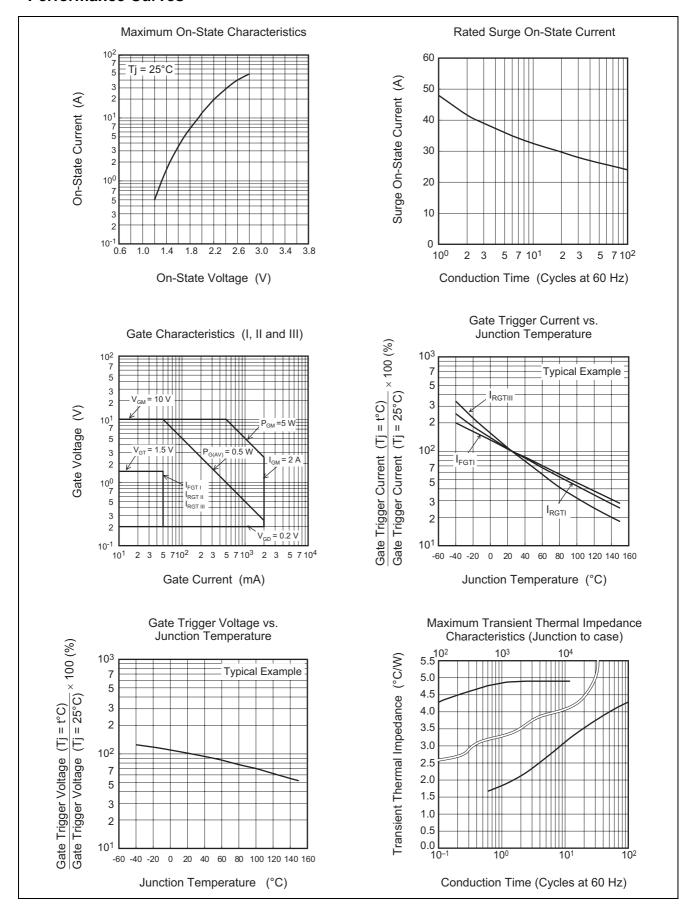
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	_	_	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V_{TM}	_	_	2.0	V	Tc = 25°C, I _{TM} = 12 A,
							Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}		_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V_{RGTI}	_	_	1.5	V	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	_	_	50	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I_{RGTI}		_	50	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	50	mA	
Gate non-trigger voltage		V_{GD}	0.2	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	4.9	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage Note4	е	(dv/dt)c	10	_	_	V/μs	Tj = 125°C

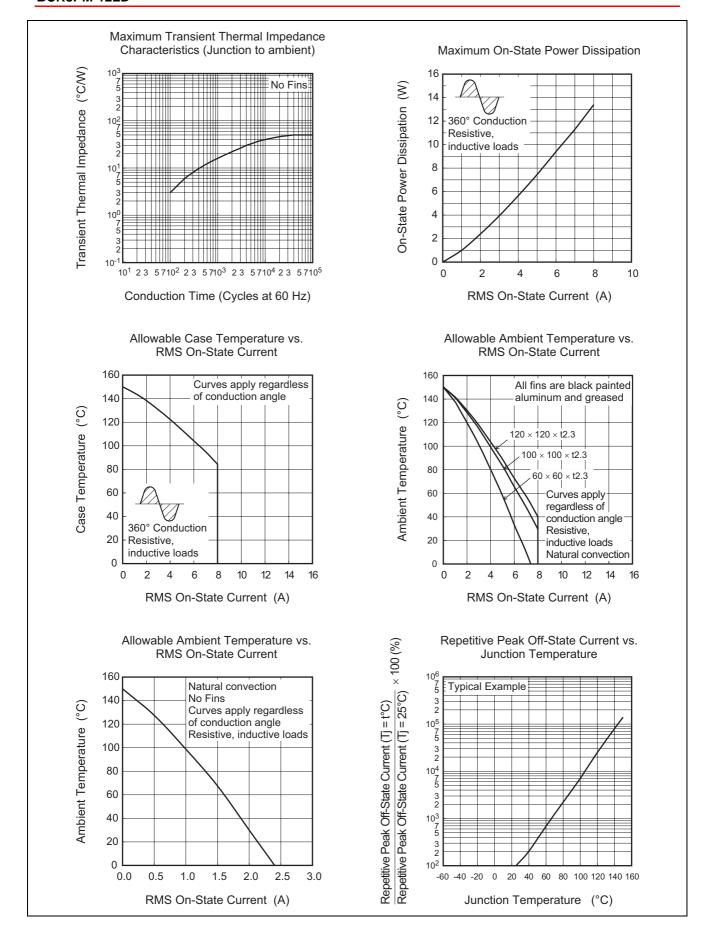
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

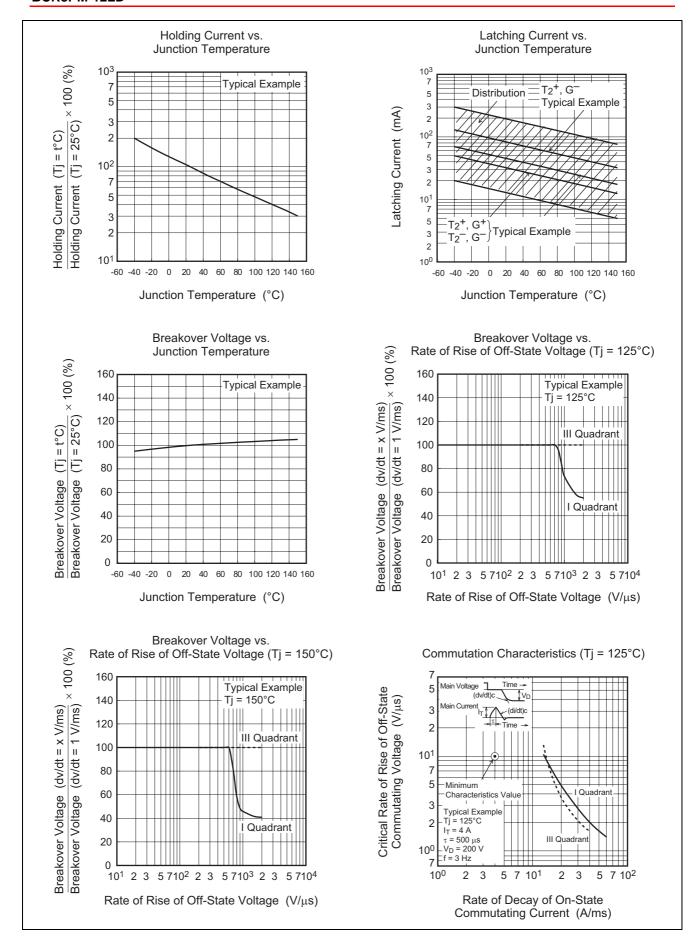
- 3. The contact thermal resistance $R_{\text{th (c-f)}}$ in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

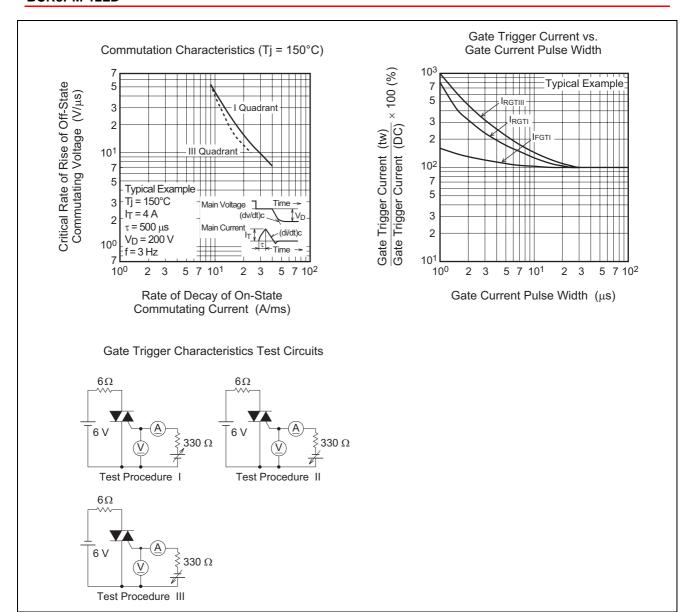
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 4 A/ms	Main Current — (di/dt)c — Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time (dv/dt)c

Performance Curves

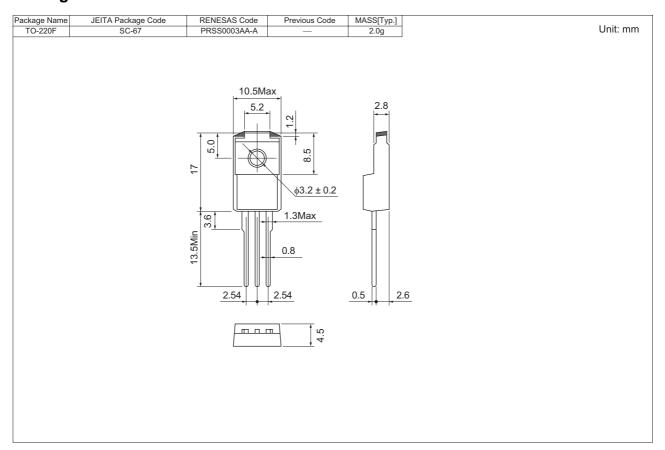








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR8PM-12LD
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-12LD-A8

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510